

L Number	Hits	Search Text	DB	Time stamp
2	1430	(gate adj electrode) and (drain adj electrode) and (source adj electrode) and (light near2 emitting)	USPAT; US-PGPUB	2004/10/27 18:02
3	581	((gate adj electrode) and (drain adj electrode) and (source adj electrode) and (light near2 emitting)) and hole and (semiconductor near2 (film or layer))	USPAT; US-PGPUB	2004/10/27 17:51
4	215	((((gate adj electrode) and (drain adj electrode) and (source adj electrode) and (light near2 emitting)) and hole and (semiconductor near2 (film or layer))) and passivation	USPAT; US-PGPUB	2004/10/27 17:51
5	106	(((((gate adj electrode) and (drain adj electrode) and (source adj electrode) and (light near2 emitting)) and hole and (semiconductor near2 (film or layer))) and passivation) and @ad<20020711	USPAT; US-PGPUB	2004/10/27 17:51
6	52	(gate adj electrode) and (drain adj electrode) and (source adj electrode) and (light near2 emitting)	EPO; JPO; DERWENT; IBM TDB	2004/10/27 18:02